

# BUK7Y102-100B

# N-channel TrenchMOS standard level FET Rev. 03 — 7 April 2010

**Product data sheet** 

# **Product profile**

### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using Nexperia High-Performance Automotive (HPA) TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- Q101 compliant
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive systems
- DC-to-DC converters

- General purpose power switching
- Solenoid drivers

#### 1.4 Quick reference data

Table 1. Quick reference data

| Symbol               | Parameter  | Conditions   | Min | Тур | Max | Unit |
|----------------------|--|--|-----|-----|-----|------|
| $V_{DS}$             | drain-source<br>voltage                            | $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$  | -   | -   | 100 | V    |
| I <sub>D</sub>       | drain current                                      | $V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$<br>see <u>Figure 1</u> ; see <u>Figure 4</u>  | -   | -   | 15  | Α    |
| P <sub>tot</sub>     | total power dissipation                            | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>   | -   | -   | 60  | W    |
| Static chara         | acteristics  |  |     |     |     |      |
| R <sub>DSon</sub>    | drain-source<br>on-state<br>resistance             | $V_{GS} = 10 \text{ V}; I_D = 5 \text{ A};$<br>$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{\text{see } \frac{\text{Figure 13}}{\text{Figure 13}}};$               | -   | 86  | 102 | mΩ   |
| Avalanche            | ruggedness   |  |     |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive<br>drain-source<br>avalanche energy | $\begin{split} I_D &= 15 \text{ A; } V_{sup} \leq 100 \text{ V;} \\ R_{GS} &= 50  \Omega;  V_{GS} = 10 \text{ V;} \\ T_{j(init)} &= 25 ^{\circ}\text{C; } unclamped \end{split}$ | -   | -   | 35  | mJ   |
| Dynamic ch           | naracteristics                                     |  |     |     |     |      |
| $Q_{GD}$             | gate-drain charge                                  | $I_D = 5 \text{ A}$ ; $V_{DS} = 80 \text{ V}$ ;<br>$V_{GS} = 10 \text{ V}$ ; see Figure 16   | -   | 4.7 | -   | nC   |



# 2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--------------------|----------------|
| 1   | S      | source                            |                    |                |
| 2   | S      | source                            | mb                 | D              |
| 3   | S      | source                            |                    |                |
| 4   | G      | gate                              |                    |                |
| mb  | D      | mounting base; connected to drain | 1 2 3 4            | mbb076 S       |
|     |        |                                   | SOT669 (LFPAK)     |                |

# 3. Ordering information

Table 3. Ordering information

| Type number   | Package |   |         |  |
|---------------|---------|---|---------|--|
|               | Name    | Description   | Version |  |
| BUK7Y102-100B | LFPAK   | plastic single-ended surface-mounted package (LFPAK); 4 leads | SOT669  |  |

# 4. Limiting values

Table 4. Limiting values

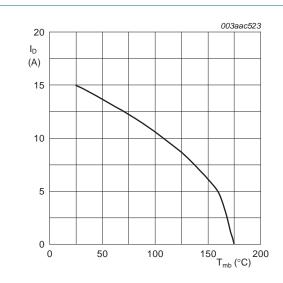
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol               | Parameter  | Conditions  |           | Min | Тур | Max  | Unit |
|----------------------|--|---|-----------|-----|-----|------|------|
| $V_{DS}$             | drain-source voltage                               | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C   |           | -   | -   | 100  | V    |
| $V_{DGR}$            | drain-gate voltage                                 | $R_{GS} = 20 \text{ k}\Omega$   |           | -   | -   | 100  | V    |
| $V_{GS}$             | gate-source voltage                                |   |           | -20 | -   | 20   | V    |
| I <sub>D</sub>       | drain current                                      | $T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u> ; see <u>Figure 4</u>  |           | -   | -   | 15   | Α    |
|                      |  | $T_{mb} = 100  ^{\circ}\text{C};  V_{GS} = 10  \text{V};  \text{see}  \frac{\text{Figure 1}}{}$   |           | -   | -   | 10.6 | Α    |
| I <sub>DM</sub>      | peak drain current                                 | $T_{mb}$ = 25 °C; $t_p \le 10$ μs; pulsed; see Figure 4   |           | -   | -   | 60   | Α    |
| P <sub>tot</sub>     | total power dissipation                            | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>  |           | -   | -   | 60   | W    |
| T <sub>stg</sub>     | storage temperature                                |   |           | -55 | -   | 175  | °C   |
| Tj                   | junction temperature                               |   |           | -55 | -   | 175  | °C   |
| Source-drain         | diode  |   |           |     |     |      |      |
| Is                   | source current                                     | T <sub>mb</sub> = 25 °C   |           | -   | -   | 15   | Α    |
| I <sub>SM</sub>      | peak source current                                | $t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$  |           | -   | -   | 60   | Α    |
| Avalanche rug        | gedness  |   |           |     |     |      |      |
| E <sub>DS(AL)S</sub> | non-repetitive<br>drain-source<br>avalanche energy | $\begin{split} I_D &= 15 \text{ A; } V_{sup} \leq 100 \text{ V; } R_{GS} = 50  \Omega; \\ V_{GS} &= 10 \text{ V; } T_{j(init)} = 25 \text{ °C; } unclamped \end{split}$ |           | -   | -   | 35   | mJ   |
| E <sub>DS(AL)R</sub> | repetitive drain-source avalanche energy           | see Figure 3  | [1][2][3] | -   | -   | -    | J    |

<sup>[1]</sup> Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

<sup>[2]</sup> Repetitive avalanche rating limited by an average junction temperature of 170 °C.

<sup>[3]</sup> Refer to application note AN10273 for further information.



03na19 120 P<sub>der</sub> (%) 80 40 0 0 100 150 200 T<sub>mb</sub> (°C)  $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$ 

Continuous drain current as a function of mounting base temperature

Normalized total power dissipation as a Fig 2. function of mounting base temperature

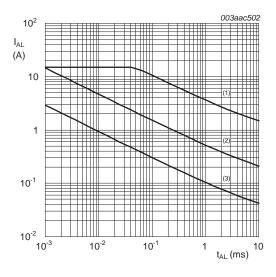
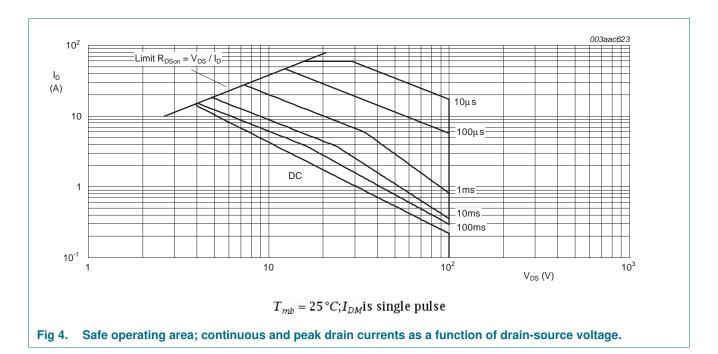


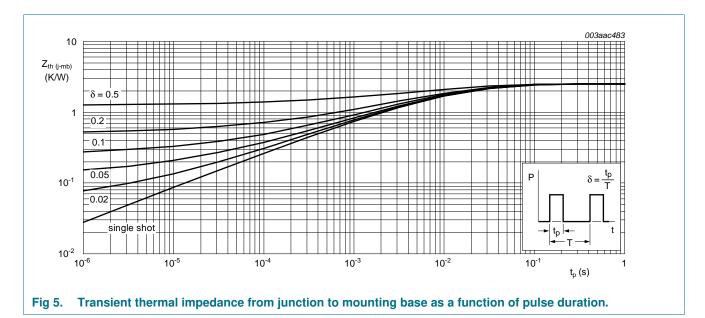
Fig 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time



### 5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter   | Conditions   | Min | Тур | Max  | Unit |
|----------------|---|--------------|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance<br>from junction to<br>mounting base | see Figure 5 | -   | -   | 2.53 | K/W  |



# 6. Characteristics

Table 6. Characteristics

| Table 6.            | Characteristics                  |   |     |      |     |      |
|---------------------|----------------------------------|---|-----|------|-----|------|
| Symbol              | Parameter                        | Conditions  | Min | Тур  | Max | Unit |
| Static cha          | racteristics                     |   |     |      |     |      |
| (011)000            | drain-source                     | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$  | 100 | -    | -   | V    |
|                     | breakdown voltage                | $I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$  | 90  | -    | -   | V    |
| $V_{GS(th)}$        | gate-source threshold voltage    | $I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C;<br>see <u>Figure 10</u> ; see <u>Figure 11</u>             | 2   | 3    | 4   | V    |
|                     |                                  | $I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 10   | -   | -    | 4.4 | V    |
|                     |                                  | $I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see Figure 10   | 1   | -    | -   | V    |
| I <sub>DSS</sub>    | drain leakage current            | $V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$   | -   | 0.02 | 1   | μΑ   |
|                     |                                  | V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C                                     | -   | -    | 500 | μΑ   |
| I <sub>GSS</sub>    | gate leakage current             | V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 20 V; T <sub>j</sub> = 25 °C                                       | -   | 2    | 100 | nA   |
|                     |                                  | V <sub>DS</sub> = 0 V; V <sub>GS</sub> = -20 V; T <sub>j</sub> = 25 °C                                      | -   | 2    | 100 | nA   |
| Doon                | drain-source on-state resistance | $V_{GS} = 10 \text{ V}$ ; $I_D = 5 \text{ A}$ ; $T_j = 175 ^{\circ}\text{C}$ ; see Figure 12; see Figure 13 | -   | -    | 265 | mΩ   |
|                     |                                  | $V_{GS} = 10 \text{ V}$ ; $I_D = 5 \text{ A}$ ; $T_j = 25 \text{ °C}$ ; see Figure 12; see Figure 13        | -   | 86   | 102 | mΩ   |
| Dynamic             | characteristics                  |   |     |      |     |      |
| Q <sub>G(tot)</sub> | total gate charge                | $I_D = 5 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$  | -   | 12.2 | -   | nC   |
| Q <sub>GS</sub>     | gate-source charge               | see Figure 16   | -   | 2.5  | -   | nC   |
| $Q_{GD}$            | gate-drain charge                |   | -   | 4.7  | -   | nC   |
| C <sub>iss</sub>    | input capacitance                | $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$   | -   | 584  | 779 | pF   |
| C <sub>oss</sub>    | output capacitance               | T <sub>j</sub> = 25 °C; see <u>Figure 14</u>  | -   | 85   | 102 | pF   |
| $C_{rss}$           | reverse transfer capacitance     |   | -   | 38   | 52  | pF   |
| t <sub>d(on)</sub>  | turn-on delay time               | $V_{DS} = 30 \text{ V}; R_L = 6 \Omega; V_{GS} = 10 \text{ V};$   | -   | 11   | -   | ns   |
| t <sub>r</sub>      | rise time                        | $R_{G(ext)} = 10 \Omega$  | -   | 4.8  | -   | ns   |
| t <sub>d(off)</sub> | turn-off delay time              |   | -   | 25   | -   | ns   |
| t <sub>f</sub>      | fall time                        |   | -   | 5.4  | -   | ns   |
| Source-d            | rain diode                       |   |     |      |     |      |
| $V_{SD}$            | source-drain voltage             | $I_S = 5 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 15                        | -   | 0.85 | 1.2 | V    |
| t <sub>rr</sub>     | reverse recovery time            | $I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$                           | -   | 51   | -   | ns   |
| Q <sub>r</sub>      | recovered charge                 | $V_{DS} = 30 \text{ V}$   | -   | 122  | -   | nC   |

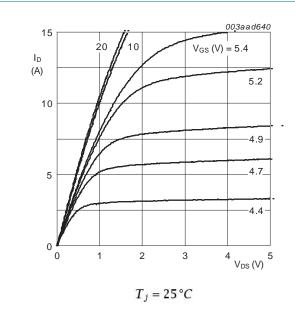


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values.

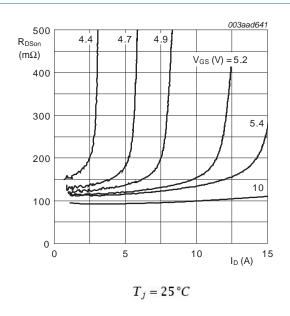


Fig 7. Drain-source on-state resistance as a function of drain current; typical values.

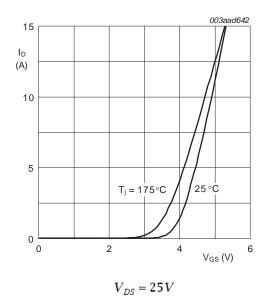


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values.

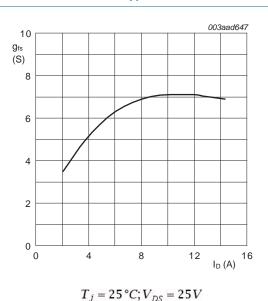


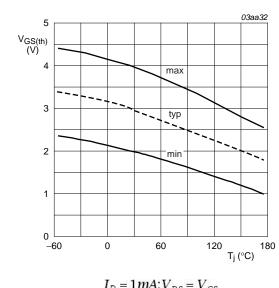
Fig 9. Forward transconductance as a function of drain current; typical values.

max

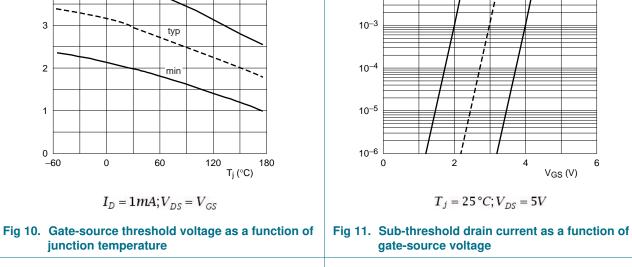
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. typ

min



junction temperature



10-1

10-2

I<sub>D</sub> (A)

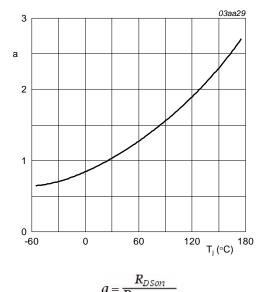


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

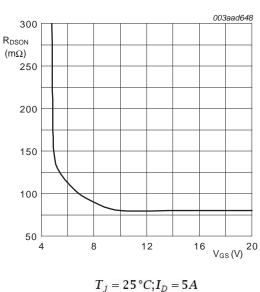


Fig 13. Drain-source on-state resistance as a function of gate-source voltage; typical values.

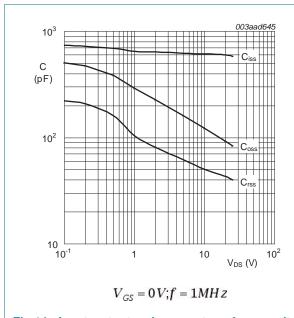


Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.

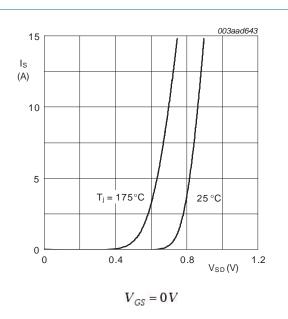
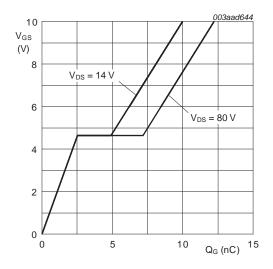


Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.



 $T_j = 25 \,^{\circ}C; I_D = 5A$ 

Fig 16. Gate-source voltage as a function of gate charge; typical values.

# Package outline

### Plastic single-ended surface-mounted package (LFPAK); 4 leads

**SOT669** 

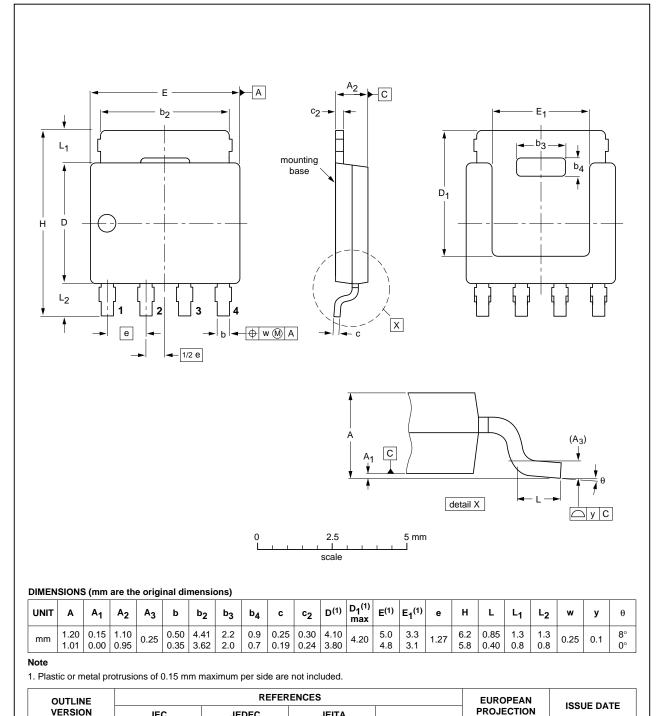


Fig 17. Package outline SOT669 (LFPAK)

IEC

JEDEC

MO-235

BUK7Y102-100B

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JEITA

04-10-13

06-03-16

VERSION

SOT669

# 8. Revision history

### Table 7. Revision history

| Document ID     | Release date                    | Data sheet status         | Change notice | Supersedes      |
|-----------------|---------------------------------|---------------------------|---------------|-----------------|
| BUK7Y102-100B_3 | 20100407                        | Product data sheet        | -             | BUK7Y102-100B_2 |
| Modifications:  | <ul> <li>Status char</li> </ul> | nged from objective to pr | oduct.        |                 |
| BUK7Y102-100B_2 | 20100215                        | Objective data sheet      | -             | BUK7Y102-100B_1 |

# 9. Legal information

#### 9.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# BUK7Y102-100B

# **Nexperia**

### N-channel TrenchMOS standard level FET

# 11. Contents

| 1   | Product profile          |
|-----|--------------------------|
| 1.1 | General description      |
| 1.2 | Features and benefits    |
| 1.3 | Applications             |
| 1.4 | Quick reference data1    |
| 2   | Pinning information2     |
| 3   | Ordering information     |
| 4   | Limiting values3         |
| 5   | Thermal characteristics5 |
| 6   | Characteristics6         |
| 7   | Package outline          |
| 8   | Revision history11       |
| 9   | Legal information12      |
| 9.1 | Data sheet status        |
| 9.2 | Definitions12            |
| 9.3 | Disclaimers              |
| 9.4 | Trademarks13             |
| 10  | Contact information      |